



Attorney's Docket No. 042390.P5771D

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

Gang Bai and Chunlin Liang

Serial No. 09/517,705

Filed: March 2, 2000

For: *Complementary Metal Gate Electrode
Technology*

Divisional Application of:

Serial No. 09/107,604

Filed: June 30, 1998

Examiner: Not yet assigned

Art Unit 2811

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SUPPLEMENTAL PRELIMINARY AMENDMENT

Box Amendments - No Fee
Assistant Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

In connection with the above-referenced Divisional Application under Rule 1.53(b),
Applicants respectfully request entry of the following amendments.

IN THE SPECIFICATION

At page 1, line 3, please replace "The", first occurrence, with --In the context of insulated

B1 gate field effect transistors, the--.

At page 1, line 11, please replace "can significantly eliminate" with --may reduce--.

At page 1, line 15, please replace "can" with --may--.

At page 1, line 18, after "etc.", please insert --Longer gate electrodes correspond to field

B2 effect transistors of greater width.--.

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